

Gerald Rescher

List of Publications by Year in descending order

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8
papers

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citations

2492102

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2266119

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8
docs citations

8
times ranked

270
citing authors

#	ARTICLE	IF	CITATIONS
1	On the origin of drain current transients and subthreshold sweep hysteresis in 4H-SiC MOSFETs. Applied Physics Letters, 2019, 115, .	1.5	2
2	NH ₃ and NO + NH ₃ Annealing of 4H-SiC Trench MOSFETs: Device Performance and Reliability. IEEE Transactions on Electron Devices, 2019, 66, 4692-4697.	1.6	12
3	Threshold voltage peculiarities and bias temperature instabilities of SiC MOSFETs. Microelectronics Reliability, 2018, 80, 68-78.	0.9	160
4	Investigation of threshold voltage stability of SiC MOSFETs. , 2018, , .		46
5	Preconditioned BTI on 4H-SiC: Proposal for a Nearly Delay Time-Independent Measurement Technique. IEEE Transactions on Electron Devices, 2018, 65, 1419-1426.	1.6	35
6	Improved Interface Trap Density Close to the Conduction Band Edge of a-Face 4H-SiC MOSFETs Revealed Using the Charge Pumping Technique. Materials Science Forum, 2017, 897, 143-146.	0.3	3
7	On the subthreshold drain current sweep hysteresis of 4H-SiC nMOSFETs. , 2016, , .		40
8	Threshold Voltage Instabilities of Present SiC-Power MOSFETs under Positive Bias Temperature Stress. Materials Science Forum, 0, 858, 481-484.	0.3	23